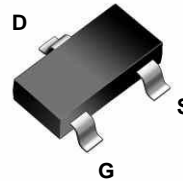
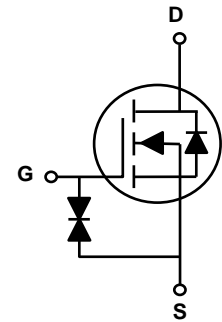


Main Product Characteristics

$V_{(BR)DSS}$	20V
$R_{DS(on)}$	300mΩ
I_D	800mA



SOT-523



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSF2320Y utilizes the latest processing techniques to achieve high cell density, low on-resistance and high repetitive avalanche rating. These features make this device extremely efficient and reliable device for use in power switching applications and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±8	V
Drain Current – Continuous (T _C =25°C)	I _D	800	mA
Drain Current – Continuous (T _C =100°C)		510	mA
Drain Current – Pulsed ¹	I _{DM}	3.2	A
Power Dissipation (T _C =25°C)	P _D	312	mW
Power Dissipation – Derate above 25°C		2.5	mW/°C
Storage Temperature Range	T _{STG}	-55 to +150	°C
Operating Junction Temperature Range	T _J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to Ambient	R _{θJA}	---	400	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	---	---	V
BV_{DSS} Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	---	-0.01	---	$V/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=16V, V_{GS}=0V, T_J=125^\circ\text{C}$	---	---	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 6V, V_{DS}=0V$	---	---	± 20	μA
On Characteristics						
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=0.5A$	---	200	300	m Ω
		$V_{GS}=2.5V, I_D=0.4A$	---	235	400	
		$V_{GS}=1.8V, I_D=0.2A$	---	295	550	
		$V_{GS}=1.5V, I_D=0.1A$	---	365	800	
		$V_{GS}=1.2V, I_D=0.1A$	---	600	1500	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.3	0.6	1.0	V
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}$		---	3	---	$\text{mV}/^\circ\text{C}$
Dynamic and Switching Characteristics						
Total Gate Charge ^{2,3}	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=0.5A$	---	1	2	nC
Gate-Source Charge ^{2,3}	Q_{gs}		---	0.26	0.5	
Gate-Drain Charge ^{2,3}	Q_{gd}		---	0.2	0.4	
Turn-On Delay Time ^{2,3}	$T_{d(on)}$	$V_{DD}=10V, V_{GS}=4.5V, R_G=10\Omega, I_D=0.5A$	---	5	10	ns
Rise Time ^{2,3}	T_r		---	3.5	7	
Turn-Off Delay Time ^{2,3}	$T_{d(off)}$		---	14	28	
Fall Time ^{2,3}	T_f		---	6	12	
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0V, F=1\text{MHz}$	---	38.2	75	pF
Output Capacitance	C_{oss}		---	14.4	28	
Reverse Transfer Capacitance	C_{rss}		---	6	12	
Drain-Source Diode Characteristics and Maximum Ratings						
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	$V_G=V_D=0V, \text{Force Current}$	---	---	0.8	A
Pulsed Source Current	I_{SM}		---	---	1.6	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.2A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

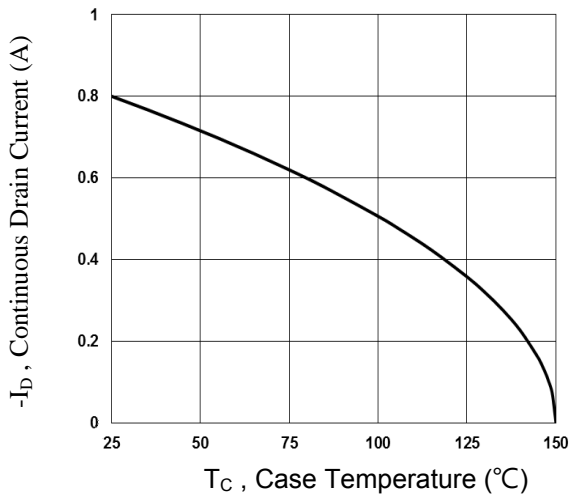


Fig.1 Continuous Drain Current vs. T_c

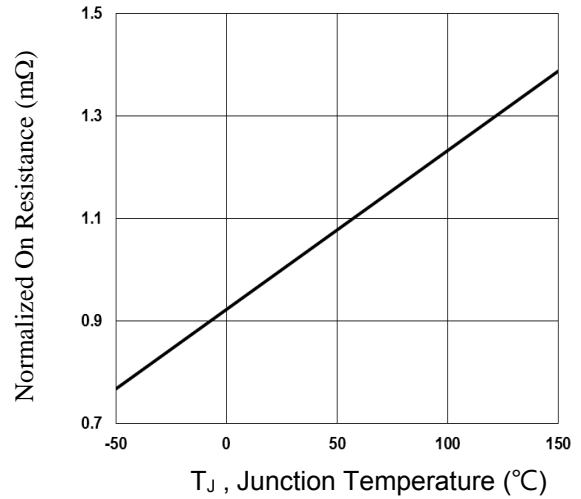


Fig.2 Normalized $R_{DS(on)}$ vs. T_j

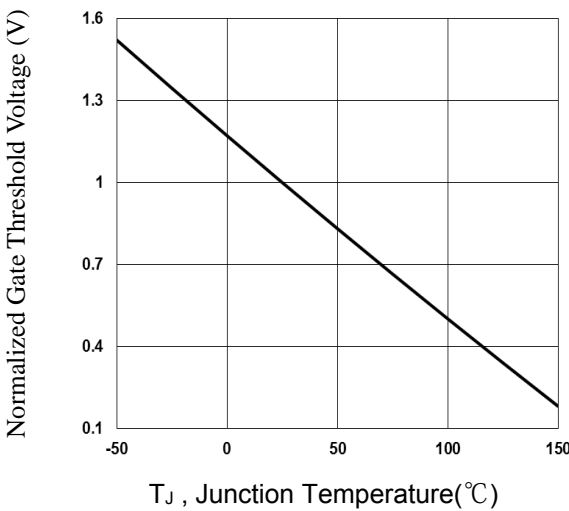


Fig.3 Normalized V_{th} vs T_j

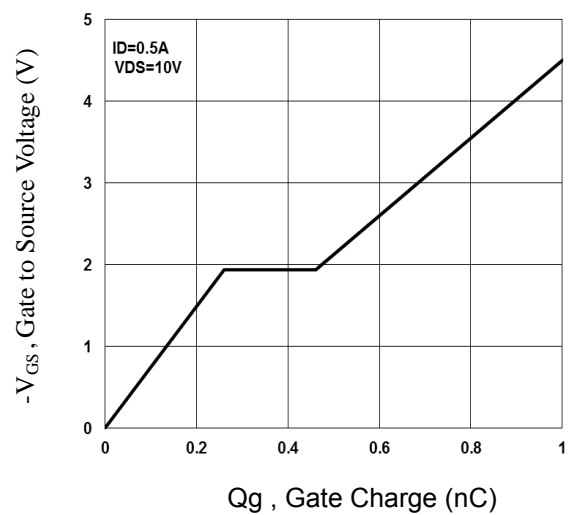


Fig.4 Gate Charge Waveform

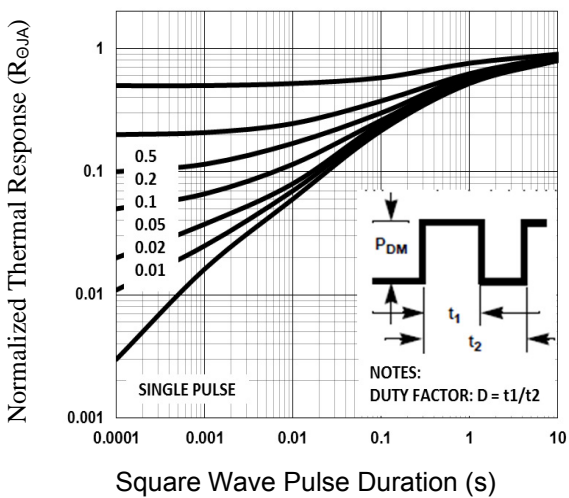


Fig.5 Normalized Transient Impedance

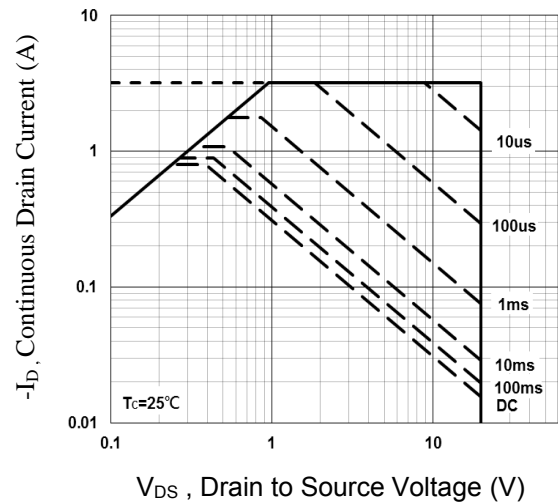


Fig.6 Maximum Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

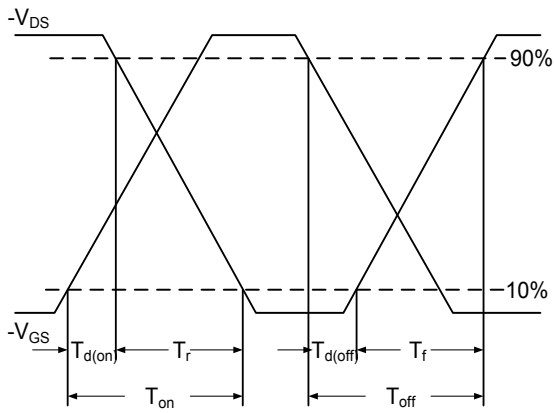


Fig.7 Switching Time Waveform

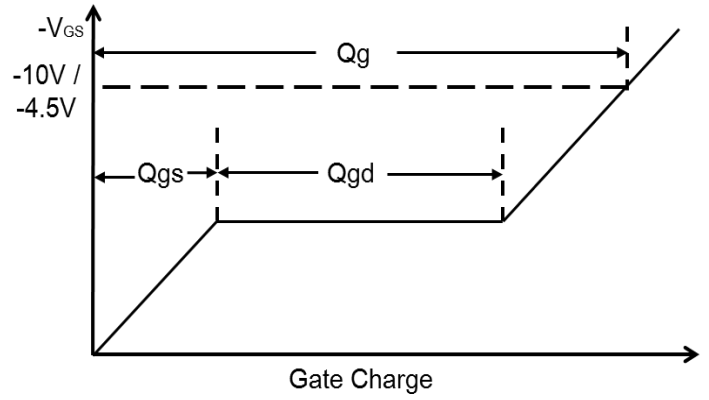
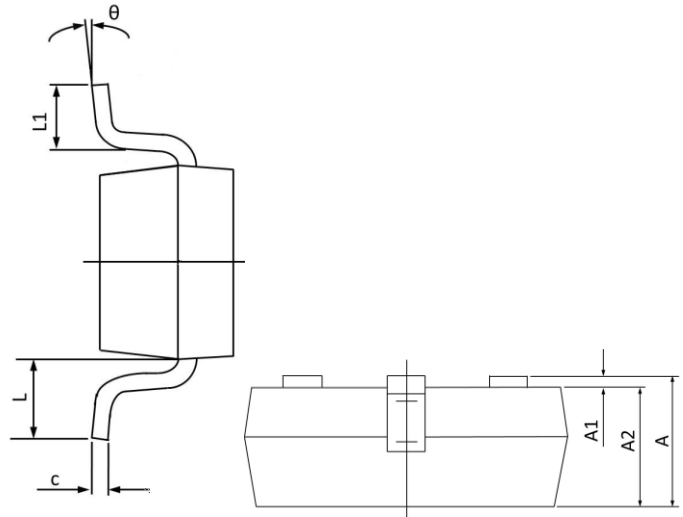
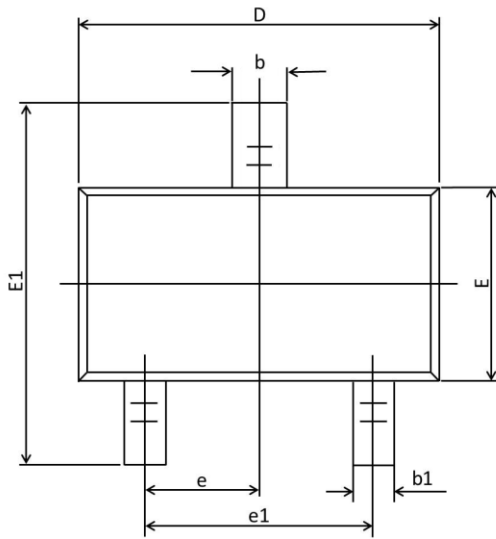


Fig.8 Gate Charge Waveform

Package Outline Dimensions

SOT-523



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	0.900	0.700	0.035	0.028
A1	0.100	0.000	0.004	0.000
A2	0.800	0.700	0.031	0.028
b	0.350	0.250	0.014	0.010
b1	0.250	0.150	0.010	0.006
c	0.200	0.100	0.008	0.004
D	1.750	1.500	0.069	0.059
E	0.900	0.700	0.035	0.028
E1	1.750	1.400	0.069	0.055
e	0.5TYP.		0.02TYP.	
e1	1.100	0.900	0.043	0.035
L	0.460	0.300	0.018	0.012
L1	0.460	0.260	0.018	0.010
θ	8°	0°	8°	0°